

IN THE SPECIFICATION:

Please amend the paragraph beginning on page 7, line 25, of the specification, as follows:

--The plasma polymerizing etch deposits polymeric materials, typically in the form of
5 layers (hereinafter "polymer layers"), on the walls of feature 210 during etching. The total
thickness of the polymer layers deposited, e.g., from about ten nanometers to about 500
nanometers, should be controlled such that the plasma polymerizing etchant species may still
diffuse through the polymer layers and etch antireflective material 204. The thickness of the
polymer layers deposited depends on the composition of the polymeric materials and whether the
10 particular surface is subject to ion bombardment. For example, during etching of feature 210, the
thickness of the polymer layers deposited during etching of radiation sensitive imaging layer 202
is greater than the thickness of the polymer layers deposited during etching of antireflective
material 204. In an exemplary embodiment, the total thickness of the polymer layers deposited
during etching of radiation sensitive imaging layer 202 is up to about four nanometers at the
15 thickest portion. For example, the total thickness of the polymer layers deposited during etching
of radiation sensitive imaging layer 202 is between about one to about three nanometers at the
thickest portion. The plasma polymerizing etch may be employed to reduce the critical
dimensions of a feature by up to about 80 nanometers during etching of the antireflective
material.--